

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently amended): A nitride based semiconductor laser device comprising:

a transparent substrate having conductive properties;

a nitride based semiconductor layer formed on one surface of said transparent substrate and constituting a cavity having a front facet on a side of laser light emission and a rear facet on an opposite side from said front facet, said front facet emitting a larger amount of light than said rear facet;

a first ohmic electrode of a first conduction type formed on the other surface of said transparent substrate; and

a second ohmic electrode of a second conduction type formed on said nitride based semiconductor layer,

wherein at least one of said first and second ohmic electrodes is formed in such ~~[[a]]~~ an asymmetrical shape or arrangement that ~~the directions of~~ the front facet and the rear facet of said cavity of said nitride based semiconductor layer can be distinguished, and

wherein one of said first and second ohmic electrodes can be observed through said transparent substrate and said nitride based semiconductor layer from the other side of said first and second ohmic electrodes.

2. (Original): The nitride based semiconductor laser device according to claim 1, wherein said first ohmic electrode and said second ohmic electrode have different shapes.
3. (Original): The nitride based semiconductor laser device according to claim 1, wherein said first ohmic electrode and said second ohmic electrode have the same shape.
4. (Original): The nitride based semiconductor laser device according to claim 1, wherein said second ohmic electrode is arranged on a region different from a region above a region where said first ohmic electrode is formed in said nitride based semiconductor layer.
5. (Original): The nitride based semiconductor laser device according to claim 1, wherein said transparent substrate is composed of gallium nitride or silicon carbide.
6. (Original): The nitride based semiconductor laser device according to claim 1, wherein said nitride based semiconductor layer contains at least one of gallium, aluminum, indium, boron, and thallium.
7. (Original): The nitride based semiconductor laser device according to claim 1, wherein at least one of said first and second ohmic electrodes is asymmetric with respect to a line passing through a center point of said cavity length and vertical to the cavity length direction.

8. (Original): The nitride based semiconductor laser device according to claim 1, wherein said nitride based semiconductor layer has a striped current injection region, and said first and second ohmic electrodes respectively have regions opposite to said striped current injection region.

9. (Original): The nitride based semiconductor laser device according to claim 1, further comprising dielectric films respectively formed at a front facet and a rear facet of said cavity.

10. (Original): The nitride based semiconductor laser device according to claim 9, wherein said dielectric films respectively formed at the front facet and the rear facet of said cavity have different reflectances.

11. (Original): The nitride based semiconductor laser device according to claim 1, wherein said nitride based semiconductor layer comprises a cladding layer of a first conduction type, an active layer, and a cladding layer of a second conduction type.

12. (Withdrawn): A method of fabricating a nitride based semiconductor laser device, comprising the steps of:

forming a nitride based semiconductor layer on a transparent substrate having conductive properties;

forming a first ohmic electrode of a first conduction type on a predetermined region on the other surface of said transparent substrate, and forming a second ohmic electrode of a second conduction type on said nitride based semiconductor layer; and

dividing said transparent substrate, together with said nitride based semiconductor layer, to form a front facet and a rear facet to form a cavity,

the step of forming the first and second ohmic electrodes comprising the step of forming at least one of the first and second ohmic electrodes in such a shape or arrangement that the forward and backward directions along the cavity length can be distinguished.

13. (Withdrawn): The method according to claim 12, further comprising respectively forming dielectric films at said front facet and said rear facet.

14. (Withdrawn): The method according to claim 12, wherein the step of forming said first and second ohmic electrodes comprises the step of forming the first ohmic electrode and the second ohmic electrode in different shapes.

15. (Withdrawn): The method according to claim 12, wherein the step of forming said first and second ohmic electrodes comprises the step of forming the first ohmic electrode and the second ohmic electrode in the same shape.

16. (Withdrawn): The method according to claim 12, wherein
the step of forming said first and second ohmic electrodes comprises the step of arranging
said second ohmic electrode on a region different from a region above a region where said first
ohmic electrode is formed in said nitride based semiconductor layer.

17. (Withdrawn): The method according to claim 12, wherein
said transparent substrate is composed of gallium nitride or silicon carbide.

18. (Withdrawn): The method according to claim 12, wherein
said nitride based semiconductor layer contains at least one of gallium, aluminum, indium,
boron, and thallium.

19. (Withdrawn): The method according to claim 12, wherein
the step of forming said first and second ohmic electrodes comprises the step of arranging
at least one of the first and second ohmic electrodes so as to be asymmetric with respect to a line
passing through a center point of said cavity length and vertical to the cavity length direction.

20. (Withdrawn): The method according to claim 12, wherein
said nitride based semiconductor layer has a striped current injection region, and
said first and second ohmic electrodes respectively have regions opposite to said striped
current injection region.

21. (Withdrawn): The method according to claim 13, wherein said dielectric films respectively formed at the front facet and the rear facet of said cavity have different reflectances.

22. (Currently amended): A nitride based semiconductor laser device comprising:
a transparent substrate having conductive properties;
a nitride based semiconductor layer formed on one surface of said transparent substrate and constituting a cavity having a front facet on a side of laser light emission and a rear facet on an opposite side from said front facet, said front facet emitting a larger amount of light than said rear facet;
facet;

a first ohmic electrode of a first conduction type formed on the other surface of said transparent substrate; and

a second ohmic electrode of a second conduction type formed on said nitride based semiconductor layer,

wherein at least one electrode of said first and second ohmic electrodes is formed in such [[a]] an asymmetrical shape or arrangement that the directions of the front facet and the rear facet of said cavity of said nitride based semiconductor layer can be distinguished, while a shape or arrangement of said one electrode can be distinguished through said transparent substrate and said nitride based semiconductor layer from the side on which the other electrode is formed.

23. (Previously presented): The nitride based semiconductor laser device according to claim 22, wherein

said first ohmic electrode and said second ohmic electrode have different shapes.

24. (Previously presented): The nitride based semiconductor laser device according to claim 22, wherein

said first ohmic electrode and said second ohmic electrode have the same shape.

25. (Previously presented): The nitride based semiconductor laser device according to claim 22, wherein

said transparent substrate is composed of gallium nitride or silicon carbide.

26. (Previously presented): The nitride based semiconductor laser device according to claim 22, wherein

said nitride based semiconductor layer contains at least one of gallium, aluminum, indium, boron, and thallium.

27. (Previously presented): The nitride based semiconductor laser device according to claim 22, wherein

at least one of said first and second ohmic electrodes is asymmetric with respect to a line passing through a center point of said cavity length and vertical to the cavity length direction.

28. (Previously presented): The nitride based semiconductor laser device according to claim 22, wherein

said nitride based semiconductor layer has a striped current injection region, and

said first and second ohmic electrodes respectively have regions opposite to said striped current injection region.

29. (Previously presented): The nitride based semiconductor laser device according to claim 22, further comprising

dielectric films respectively formed at a front facet and a rear facet of said cavity.

30. (Previously presented): The nitride based semiconductor laser device according to claim 29, wherein

said dielectric films respectively formed at the front facet and the rear facet of said cavity have different reflectances.

31. (Previously presented): The nitride based semiconductor laser device according to claim 22, wherein

said nitride based semiconductor layer comprises a cladding layer of a first conduction type, an active layer, and a cladding layer of a second conduction type.

32. (Currently amended): A nitride based semiconductor laser device comprising:
a transparent substrate having conductive properties;
a nitride based semiconductor layer formed on one surface of said transparent substrate and constituting a cavity having a front facet on a side of laser light emission and a rear facet on an

opposite side from said front facet, said front facet emitting a larger amount of light than said rear facet;

a first ohmic electrode of a first conduction type formed on the other surface of said transparent substrate; and

a second ohmic electrode of a second conduction type formed on said nitride based semiconductor layer,

wherein said second ohmic electrode is protruded from a region where said first ohmic electrode is formed when said nitride based semiconductor laser device is observed from the side of said nitride based semiconductor layer, and

said first ohmic electrode is protruded from a region where said second ohmic electrode is formed when said nitride based semiconductor laser device is observed from the side of said transparent substrate.

33. (Previously presented): The nitride based semiconductor laser device according to claim 32, wherein

said first ohmic electrode and said second ohmic electrode have different shapes.

34. (Previously presented): The nitride based semiconductor laser device according to claim 32, wherein

said first ohmic electrode and said second ohmic electrode have the same shape.

35. (Previously presented): The nitride based semiconductor laser device according to claim 32, wherein

said transparent substrate is composed of gallium nitride or silicon carbide.

36. (Previously presented): The nitride based semiconductor laser device according to claim 32, wherein

said nitride based semiconductor layer contains at least one of gallium, aluminum, indium, boron, and thallium.

37. (Previously presented): The nitride based semiconductor laser device according to claim 32, wherein

at least one of said first and second ohmic electrodes is asymmetric with respect to a line passing through a center point of said cavity length and vertical to the cavity length direction.

38. (Previously presented): The nitride based semiconductor laser device according to claim 32, wherein

said nitride based semiconductor layer has a striped current injection region, and

said first and second ohmic electrodes respectively have regions opposite to said striped current injection region.

39. (Previously presented): The nitride based semiconductor laser device according to claim 32, further comprising

dielectric films respectively formed at a front facet and a rear facet of said cavity.

40. (Previously presented): The nitride based semiconductor laser device according to claim 39, wherein

said dielectric films respectively formed at the front facet and the rear facet of said cavity have different reflectances.

41. (Previously presented): The nitride based semiconductor laser device according to claim 32, wherein

said nitride based semiconductor layer comprises a cladding layer of a first conduction type, an active layer, and a cladding layer of a second conduction type.